

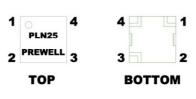
# **PLN25** GaAs p-HEMT LNA

#### Features

- 🔶 2300 2700MHz
- → 12.0 dB Gain at 2300MHz
- + +30.0 dBm Output IP3
- ✤ 0.75 dB Noise Figure at 2300MHz
- ✤ 5.5x5.5 size / No matching circuit needed
- Low power consumption (3V/45mA)
- Surface mount type

Applications
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- LNA for PCS
- Repeater
- Base Station
- Mobile Infrastructure



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C 912905
C 91302
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**Functional Diagram** 

Function	Pin No.		
RF IN	1		
RF OUT	3		
Vcc	4		
Ground	2		

## Description

The PLN25 is a high performance GaAs p-HEMT LNA (Low Noise Amplifier). The amplifier features high linear performance, low noise figure, low power consumption and high reliability. The PLN25 operates from a single voltage supply and no matching circuit needed. The device is a superior performance p-HEMT amplifier that offers high dynamic range in a low cost miniature surface mount type with metal cover. These PLN series provide the most suitable solutions for LNA in communication systems.

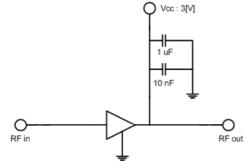
# **Specifications**

Symbol	Parameters	Units	Freq.	Min.	Тур.	Max.
S21	Gain	dB	2300 MHz		12.0	
			2700 MHz		11.0	
S11	Input Poturn Loss	dB	2300 MHz		-18	
511	Input Return Loss dB	2700 MHz		-15		
S22	Output Return Loss	dB	2300 MHz		-9	
522	Output Return Loss		2700 MHz		-10	
P1dB	Output Power @1dB	dBm	2300 MHz		15	
	compression	abiii	2700 MHz		15	
OIP3	Output Third Order	dBm	2300 MHz		30.0	
	intercept		2700 MHz		31.0	
NF	Noise Figure c	dB	2300 MHz		0.65	
		UB	2700 MHz		0.65	
V/I	Device Voltage / Current	V/mA			3.0/45	

Test Conditions : T=25°C, Supply Voltage=+3.0V, 50ohm System, OIP3 measured with two tones at an output power of 0dBm/tone separated by 1MHz.

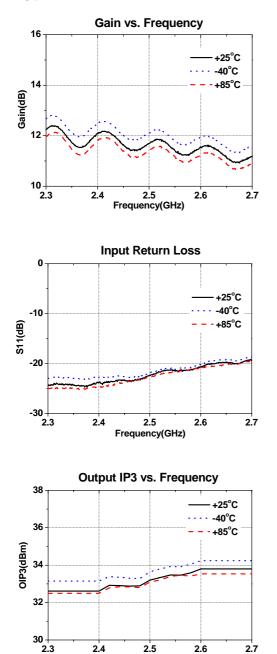


## **Application Circuit**



- Bypass Capacitors(10nF & 1uF) should be added 1. for bypassing the AC noise 2. No matching circuit needed

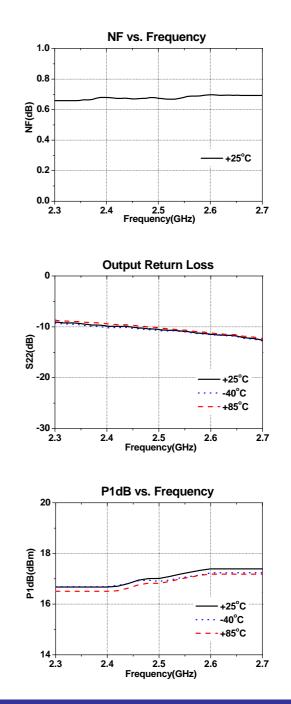
# **Typical RF Performance**



2.4

2.5

Frequency(GHz)



2.7

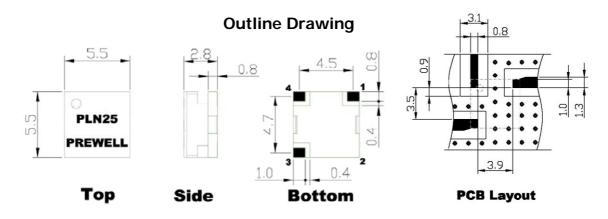
2.6



# Absolute Maximum Ratings

Parameter	Rating	Unit
Device Voltage	6	v
Device Current	80	mA
RF Power Input	10	dBm
Storage Temperature	-55 to +125	°C
Ambient Operating Temperature	-40 to +85	°C

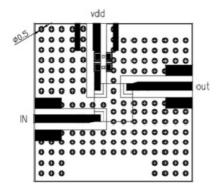
Operation of this device above any of these parameters may cause permanent damage.

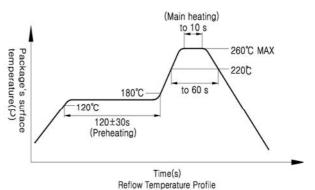


### **Soldering Time Profile**

- 1. Maximum temperature: +260°C or below.
- 2. Time at maximum temperature: 10s or less
- 3. Time of temperature higher than +220°C : 60s or less
- 4. Preheating time at +120°C to +180°C: 120±30s
- 5. Maximum number of reflow process : 3times
- 6. Maximum chlorine content of rosin flux (percentage mass) : 0.2% or less

#### **Evaluation Board Layout (2.3x2.3)**





#### **Mounting Instructions**

- 1. Use a large ground pad area with many plated through-holes as shown.
- 2. We recommend 1 oz copper minimum.
- 3. Measurement for our datasheet was made on 0.8mm thick FR-4 Board.
- 4. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
- 5. RF trace width depends on the board material and construction.
- 6. All area of GND PAD should be connected to GND